



#### 30V N-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

BV <sub>DSS</sub>	Rds(on) max	I <sub>D MAX</sub> T <sub>A</sub> = +25°C
30V	17mΩ @ V <sub>GS</sub> = 10V	8.4A
300	28mΩ @ V <sub>GS</sub> = 4.5V	6.8A

#### **Features**

- 0.6mm Profile Ideal for Low Profile Applications
- PCB Footprint of 4mm<sup>2</sup>
- Low Gate Threshold Voltage
- Low On-Resistance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMT3020LFDFQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

## **Description and Applications**

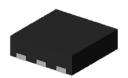
This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- **Power Management Functions**
- General Purpose Interfacing Switch

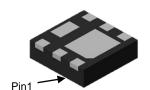
### **Mechanical Data**

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @4
- Weight: 0.0065 grams (Approximate)

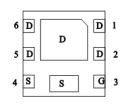
#### U-DFN2020-6 (Type F)



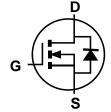




**Bottom View** 



Pin Out **Bottom View** 



**Equivalent Circuit** 

### **Ordering Information** (Note 4)

Part Number	Case	Packaging
DMT3020LFDFQ-7	U-DFN2020-6 (Type F)	3,000/Tape & Reel
DMT3020LFDFQ-13	U-DFN2020-6 (Type F)	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



## **Marking Information**

Site1

#### U-DFN2020-6 (Type F)



J6 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: H = 2020) M = Month (ex: 9 = September)

Date Code Key

Year	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031
Code	Н		J	K	L	М	N	0	Р	R	S	T
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

Site 2



J6 = Product Type Marking Code YWX = Date Code Marking Y = Year (ex: 0 = 2020) W = Week (ex: a = Week 27; z Represents Week 52 and 53) X = Internal Code (ex: U = Monday)

Date Code Key

Year	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031
Code	0	1	2	3	4	5	6	7	8	9	0	1

Week	1-26	27-52	53
Code	A-Z	a-z	z

Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Code	Т	U	V	W	X	Y	Z



# 

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage			$V_{DSS}$	30	V
Gate-Source Voltage			Vgss	±20	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10.0V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	ID	8.4 6.7	А
Continuous Drain Current (Note 6) V <sub>GS</sub> = 4.5V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	lo	6.8 5.4	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%	)		I <sub>DM</sub>	40	Α
Maximum Body Diode Continuous Current (Note 6)	Is	2	Α		
Avalanche Current (Note 7) L = 0.1mH	I <sub>AS</sub>	11.4	Α		
Avalanche Energy (Note 7) L = 0.1mH			Eas	6.5	mJ

## **Thermal Characteristics**

Characteristic		Symbol	Value	Unit	
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	D-	0.7	W	
Total Power Dissipation (Note 5)	$T_A = +70$ °C	P <sub>D</sub>	0.4	VV	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	RθJA	180	°C/W	
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	D-	1.8	W	
Total Power Dissipation (Note 6)	$T_A = +70$ °C	PD	1.1	VV	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	RθJA	70	°C/W	
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C	

## Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

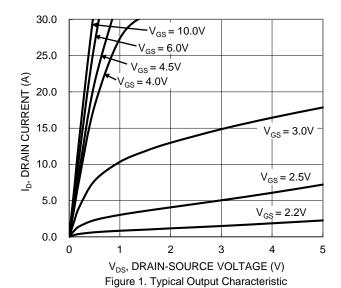
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30.0		_	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	IDSS		l	1.0	μΑ	V <sub>DS</sub> = 24V, V <sub>GS</sub> = 0V
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	Vgs(TH)	1.0		2.5	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$
Static Drain-Source On-Resistance	D- c/c/		13	17	mΩ	$V_{GS} = 10V, I_D = 9.0A$
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>		21	28	11122	$V_{GS} = 4.5V, I_{D} = 7.0A$
Diode Forward Voltage	$V_{SD}$			1.2	V	$V_{GS} = 0V$ , $I_S = 2A$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	Ciss		393	_	pF	\\\ 45\\\\\\ 0\\\
Output Capacitance	Coss		173	_	pF	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, -f = 1.0MHz
Reverse Transfer Capacitance	Crss		27	_	pF	1 – 1.0101112
Gate Resistance	Rg	_	1.1	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1.0MHz$
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	l	7.0	_	nC	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	l	3.6	_	nC	Vpp = 15V. Ip = 9A
Gate-Source Charge	Qgs	_	0.9	_	nC	VDD = 15V, ID = 9A
Gate-Drain Charge	Qgd	_	1.5	_	nC	
Turn-On Delay Time	tD(ON)	_	1.8	_	ns	
Turn-On Rise Time	t <sub>R</sub>	_	1.9	_	ns	V <sub>DD</sub> = 15V, V <sub>GS</sub> = 10V,
Turn-Off Delay Time	t <sub>D</sub> (OFF)	_	7.5	_	ns	$R_g = 6\Omega$ , $I_D = 9A$
Turn-Off Fall Time	t <sub>F</sub>	_	2.4	_	ns	]
Reverse Recovery Time	trr	_	10	_	ns	I_ 00 dI/dt 4000///-
Reverse Recovery Charge	Q <sub>RR</sub>	_	2.6	_	nC	IF = 9A, dl/dt = 100A/µs

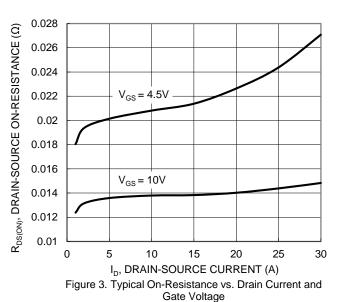
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

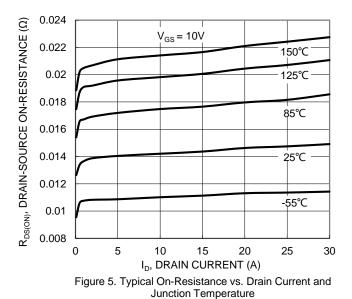
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
- 7.  $I_{AS}$  and  $E_{AS}$  ratings are based on low frequency and duty cycles to keep  $T_J$  = +25°C.
- 8. Short duration pulse test used to minimize self-heating effect.
- 9. Guaranteed by design. Not subject to product testing.

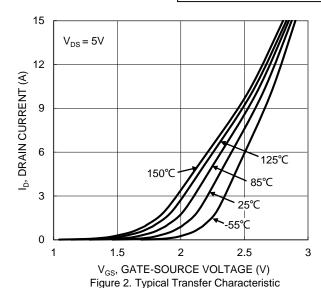
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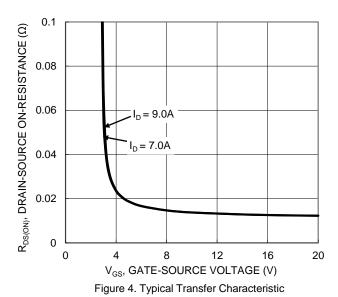












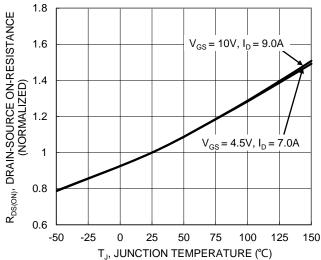


Figure 6. On-Resistance Variation with Junction
Temperature



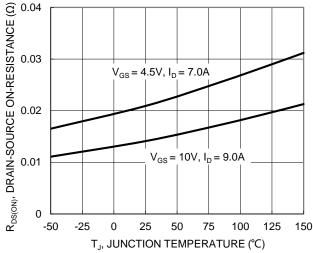
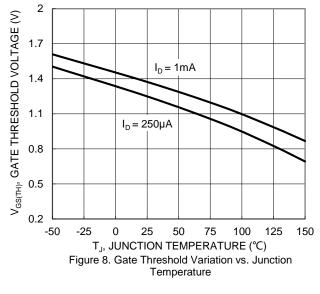
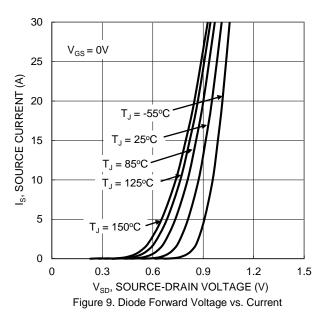
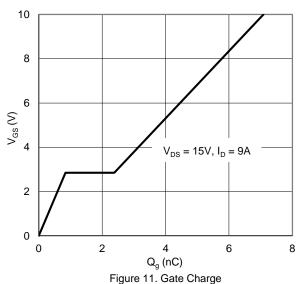
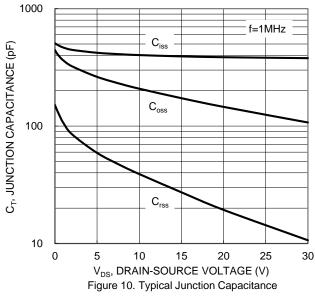


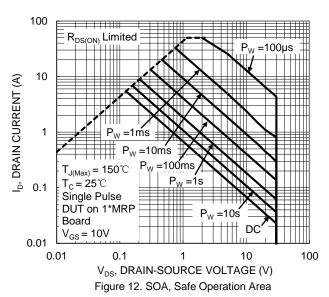
Figure 7. On-Resistance Variation with Junction Temperature













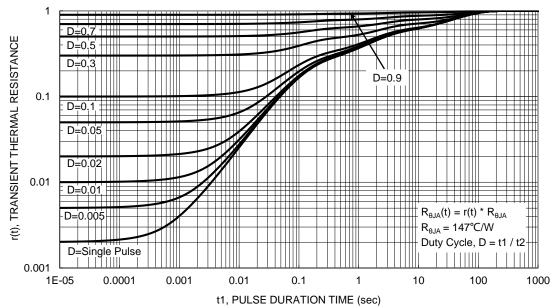


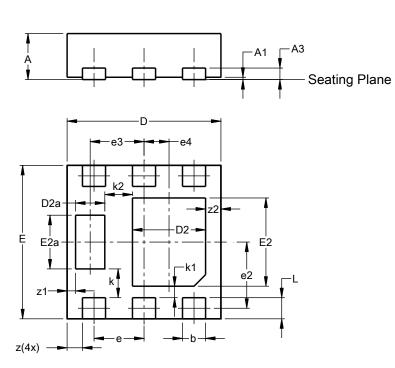
Figure 13. Transient Thermal Resistance



## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### U-DFN2020-6 (Type F)

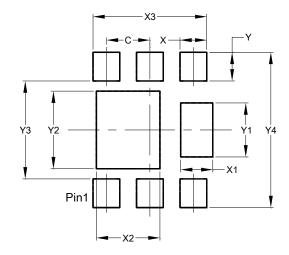


U-DFN2020-6						
		e F)	Тур			
Dim	Min	Min Max				
Α	0.57	0.63	0.60			
<b>A</b> 1	0.00	0.05	0.03			
А3	-	1	0.15			
b	0.25	0.35	0.30			
D	1.95	2.05	2.00			
D2	0.85	1.05	0.95			
D2a	0.33	0.43	0.38			
Е	1.95	2.05	2.00			
E2	1.05	1.25	1.15			
E2a	0.65	0.75	0.70			
е	(	0.65 BS	С			
e2	C	.863 BS	SC			
е3	(	0.70 BS	С			
e4	C	.325 BS	SC			
k	(	0.37 BS	С			
k1	(	0.15 BS	С			
k2	(	0.36 BS	С			
L	0.225	0.325	0.275			
Z	0.20 BSC					
<b>z</b> 1	C	.110 BS	SC			
z2	(	0.20 BS	С			
All C	imens	ions in	mm			

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### U-DFN2020-6 (Type F)



Dimensions	Value (in mm)
С	0.650
X	0.400
X1	0.480
X2	0.950
Х3	1.700
Υ	0.425
Y1	0.800
Y2	1.150
Y3	1.450
Y4	2.300



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